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(54) **Title:** CMOS DEVICE WITH DUAL-EPI CHANNELS AND SELF-ALIGNED CONTACTS

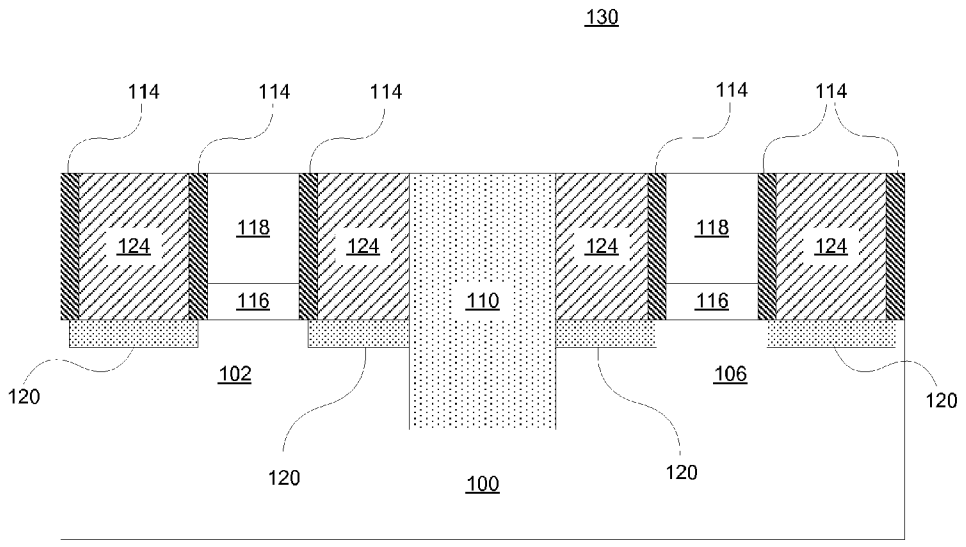


FIG._1

(57) **Abstract:** A CMOS device having dual-epi channels comprises a first epitaxial region formed on a substrate, a PMOS device formed on the first epitaxial region, a second epitaxial region formed on the substrate, wherein the second epitaxial region is formed from a different material than the first epitaxial region, an NMOS device formed on the second epitaxial region, and electrical contacts coupled to the PMOS and NMOS devices, wherein the electrical contacts are self-aligned.

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